



NPN Epitaxial Silicon Transistor

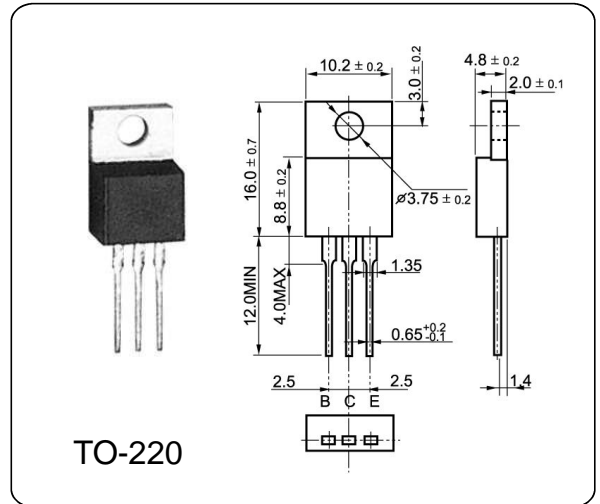
BU406

High Voltage Switching

* Use In Horizontal Deflection Output Stage

Absolute Maximum Ratings (Ta = 25)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	200	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	7.0	A
Base Current	I_B	4.0	A
Total Dissipation at	P_{tot}	60	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C



Electrical Characteristics (Ta = 25)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CES}	$V_{CE}=400V, I_E=0$			5.0	mA
		$V_{CE}=250V, I_E=0$			0.1	
Emitter Cut-off Current	I_{EBO}	$V_{EB}=6V, I_C=0$			1.0	mA
Collector-Emitter Sustaining Voltage	V_{CEO}	$I_C=50mA, I_B=0$	200			V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=4V, I_C=1.0A$	10			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=5.0A, I_B=0.5A$			1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=5.0A, I_B=0.5A$			1.2	V
Current Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=0.5A$	10			MHz
Turn Off Time	t_{OFF}	$I_C=5A, I_B=0.5A$			0.75	us